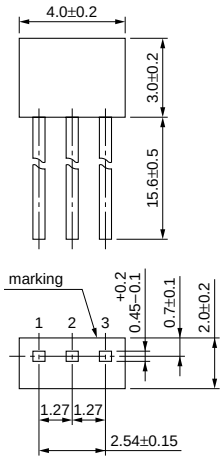
2SD2460

Silicon NPN epitaxial planer type

For low-frequency output amplification

Unit: mm



1:Emitter
2:Collector
3:Base

EIAJ:SC–72
New S Type Package

Features

- High foward current transfer ratio h_{FE}.
- Low collector to emitter saturation voltage $V_{CE(sat)}$.
- Allowing supply with the radial taping.

Absolute Maximum Ratings (Ta=25˚C)

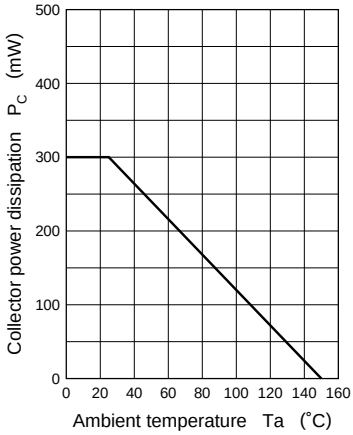
Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	20	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	15	V
Peak collector current	I_{CP}	1.5	A
Collector current	I_C	0.7	A
Collector power dissipation	P_C	300	mW
Junction temperature	T_j	150	˚C
Storage temperature	T_{stg}	–55 ~ +150	˚C

Electrical Characteristics (Ta=25˚C)

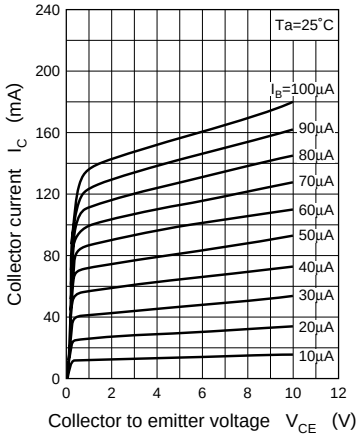
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = 15V, I_E = 0			1	μA
	I_{CEO}	V_{CE} = 15V, I_B = 0			10	μA
Collector to base voltage	V_{CBO}	I_C = 10μA, I_E = 0	20			V
Collector to emitter voltage	V_{CEO}	I_C = 1mA, I_B = 0	20			V
Emitter to base voltage	V_{EBO}	I_E = 10μA, I_C = 0	15			V
Forward current transfer ratio	h_{FE}	V_{CE} = 10V, I_C = 150mA*	1000		2500	
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = 500mA, I_B = 50mA*		0.15	0.4	V
Transition frequency	f_T	V_{CB} = 20V, I_E = –20mA, f = 200MHz		55		MHz
Collector output capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz		10	15	pF

* Pulse measurement

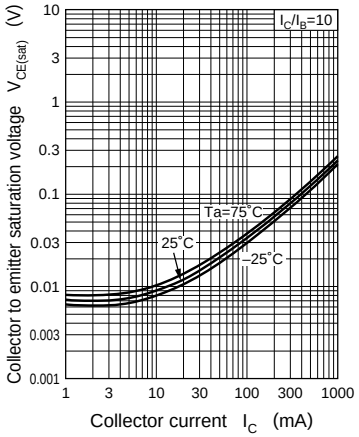
P_C — Ta



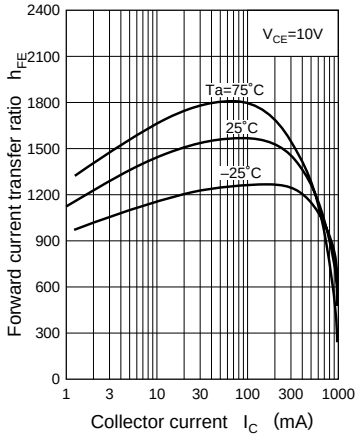
I_C — V_{CE}



$V_{CE(sat)}$ — I_C



h_{FE} — I_C



C_{ob} — V_{CB}